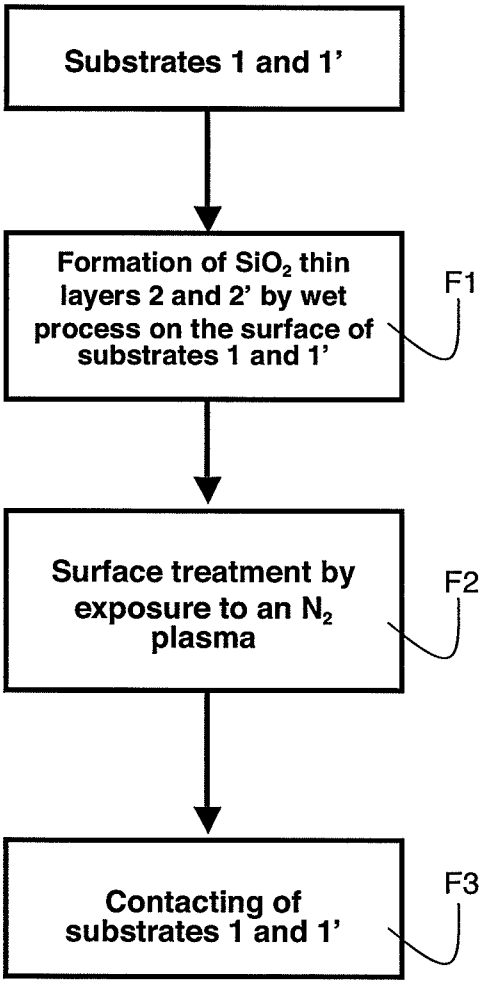

Substrates 1 and 1'
Formation of SiO_2 thin layers 2 and 2' by wet process on the surface of substrates 1 and 1'
F1
Surface treatment by exposure to an N_2 plasma
F2
Contacting of substrates 1 and 1'
F3

Fig. 1

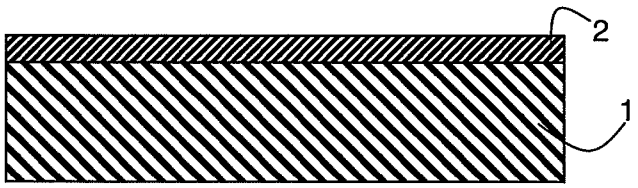


Fig. 2

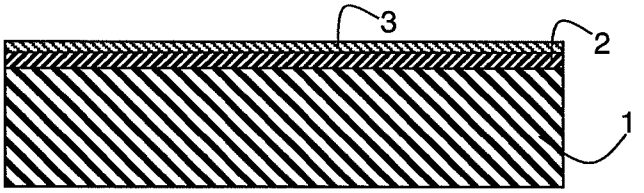


Fig. 3

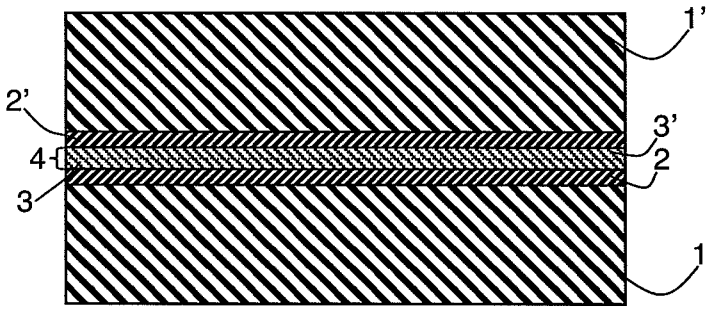


Fig. 4

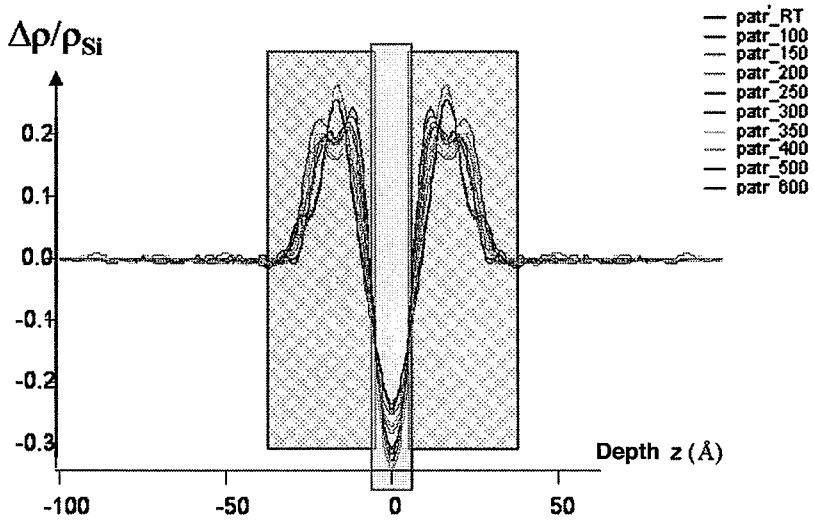

Δρ/ρSi
0.2
0.1
0.0
-0.1
-0.2
-0.3
-100
-50
0
50
Depth z (Å)
patr_RT
patr_100
patr_150
patr_200
patr_250
patr_300
patr_350
patr_400
patr_500
patr 600

Fig. 5

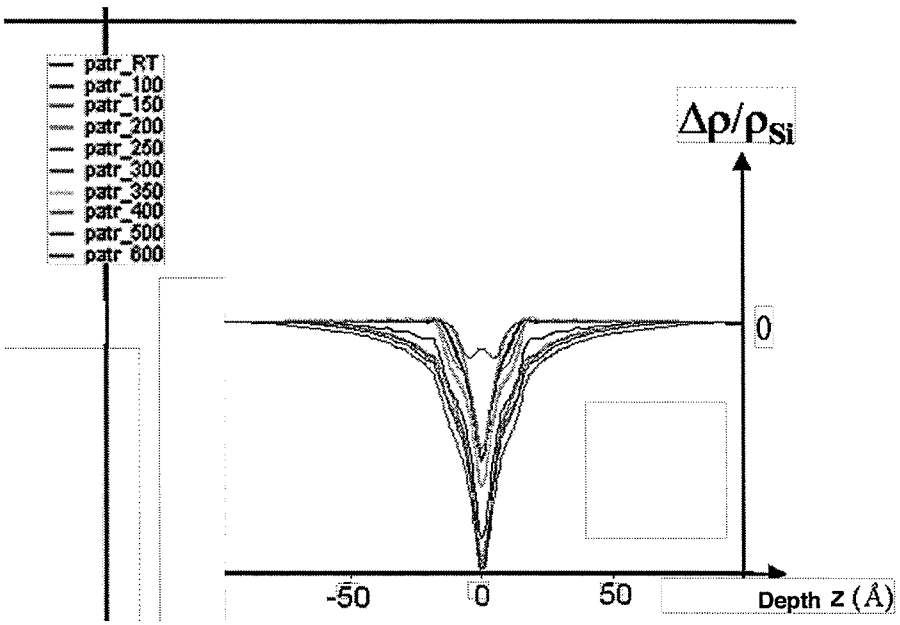

patr_RT
patr_100
patr_150
patr_200
patr_250
patr_300
patr_350
patr_400
patr_500
patr 600
Δρ/ρSi
0
-50
0
50
Depth z (Å)

Fig. 6

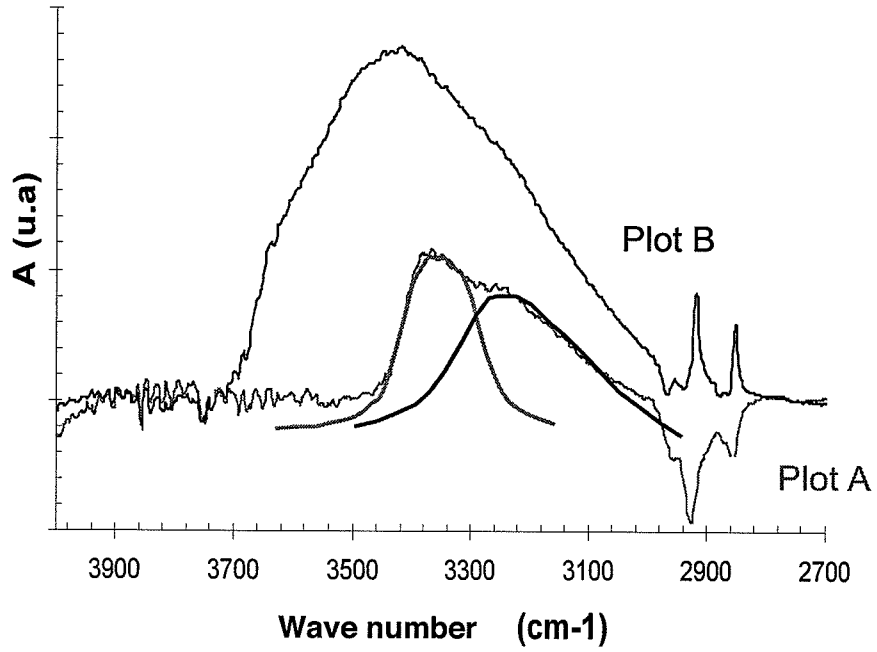

A (u.a)
Plot B
Plot A
3900
3700
3500
3300
3100
2900
2700
Wave number (cm-1)

Fig. 7